

**NONVOLATILE SEMICONDUCTOR MEMORY DEVICE AND ONE-TIME
PROGRAMMING CONTROL METHOD THEREOF**

ABSTRACT OF THE DISCLOSURE

5 A nonvolatile semiconductor memory device is provided, comprising a
nonvolatile memory cell array which has a one-time programming region
accessed in response to a first decoding signal and a normal region accessed in
response to a second decoding signal. The device performs a read operation
and a write operation. The device further comprises (a) a data write circuit
10 writing data in the nonvolatile memory cell array in response to a write enable
signal during the write operation; (b) a data read circuit reading data output from
the nonvolatile memory cell array in response to a sense amplifier enable signal
during the read operation; and (c) a control means activating the sense amplifier
enable signal when the first decoding signal is generated and comparing data
15 output from the data read circuit to generate the write enable signal during the
write operation.